

ABSTRACT

ION SOURCE HAVING REPLACEABLE AND SPUTTERABLE SOLID SOURCE MATERIAL

An ion source (10) for an ion implanter is provided, comprising:

(i) an ionization chamber (14) defined at least partially by chamber walls (12), and having an inlet (45) into which a sputtering gas may be injected and an aperture (18) through which an ion beam (B) may be extracted; (ii) an ionizing electron source (44) for ionizing the sputtering gas to form a sputtering plasma; and (iii) a sputterable repeller (100). The sputterable repeller both (a) repels electrons emitted by the electron source, and (b) provides a source of sputtered material that can be ionized by the electron source. The sputterable repeller (100) comprises a slug (108) of sputterable material, and further comprises mounting structure (102, 104) for removably mounting the slug within the ionization chamber (14), so that the slug is made removably detachable from the mounting structure. The sputterable material may be any of the following elements, or compounds including any of these elements: aluminium (Al), boron (B), beryllium (Be), carbon (C), caesium (Cs), germanium, (Ge), molybdenum, (Mo), antimony (Sb), or silicon (Si). The repeller (100) is negatively biased with respect to the ionization chamber walls (12), and may be continuously variably biased to provide for a wide dynamic range of resulting ion beam currents.

Figure 2